N-Channel 25 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a, e]	Q_g (Typ.)
25	0.0029 at V_{GS} = 10 V	65	17.5 nC
	0.0034 at V_{GS} = 4.5 V	58	

FEATURES

- TrenchFET Ⅱ Power MOSFET
- 100 % R_g and UIS Tested

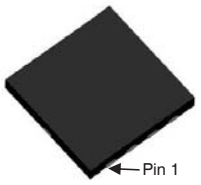
RoHS COMPLIANT

APPLICATIONS

- Notebook PC Core
- VRM/POL

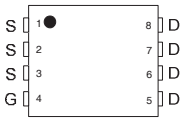
DFN 3x3 EP

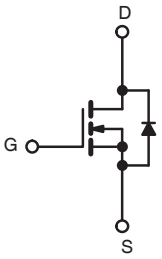
Top View



Bottom View

Top View





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	25	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	65[a, e]	A
	T_C = 70 °C		58[e]	
	T_A = 25 °C		36[b, c]	
	T_A = 70 °C		29[b, c]	
Pulsed Drain Current		I_{DM}	260	
Avalanche Current Pulse	L = 0.1 mH	I_{AS}	20	
Single Pulse Avalanche Energy		E_{AS}	25	mJ
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	65[a, e]	A
	T_A = 25 °C		5.1[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	49	W
	T_C = 70 °C		35	
	T_A = 25 °C		4.6[b, c]	
	T_A = 70 °C		3.9[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	25	35	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	2.5	4	

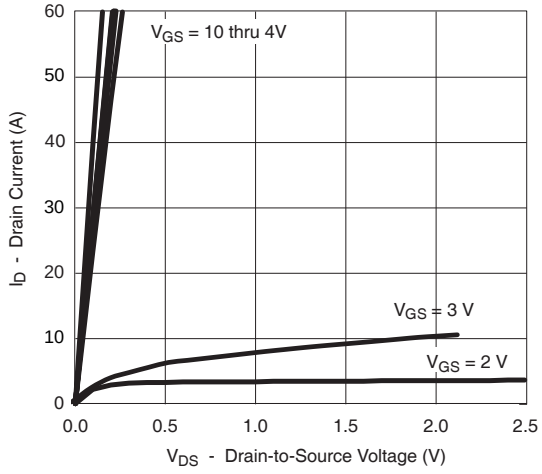
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 80 A.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min .**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	25			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.5		2.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	65			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15 A		0.0029	0.0038	Ω
		V_{GS} = 4.5 V, I_D = 10 A		0.0034	0.0040	
Forward Transconductance[a]	g_{fs}	V_{DS} = 20 V, I_D = 15A		90		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS}= 20 V, V_{GS} = 0 V, f = 1 MHz		2059		pF
Output Capacitance	C_{oss}			698		
Reverse Transfer Capacitance	C_{rss}			161		
Total Gate Charge	Q_g	V_{DS} = 20 V, V_{GS} = 10 V, I_D = 15 A		30		nC
		V_{DS} = 20 V, V_{GS} = 4.5 V, I_D = 10 A		17.5		
Gate-Source Charge	Q_{gs}			6		
Gate-Drain Charge	Q_{gd}			3.5		
Gate Resistance	R_g	f = 1 MHz		1.0	2.1	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L = 0.555 Ω $I_D \cong$ 15 A, V_{GEN} = 10 V, R_g = 1 Ω		12	25	ns
Rise Time	t_r			26	57	
Turn-Off Delay Time	$t_{d(off)}$			18	35	
Fall Time	t_f			10	25	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L = 0.625 Ω $I_D \cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω		22	43	
Rise Time	t_r			60	130	
Turn-Off Delay Time	$t_{d(off)}$			15	33	
Fall Time	t_f			12	28	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			65	A
Pulse Diode Forward Current[a]	I_{SM}				260	
Body Diode Voltage	V_{SD}	I_S = 12 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, di/dt = 100 A/µs, T_J = 25 °C		29	58	ns
Body Diode Reverse Recovery Charge	Q_{rr}			16	32	nC
Reverse Recovery Fall Time	t_a			12		ns
Reverse Recovery Rise Time	t_b			17		

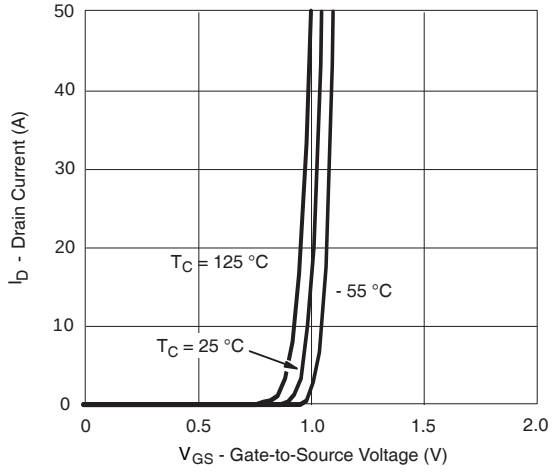
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

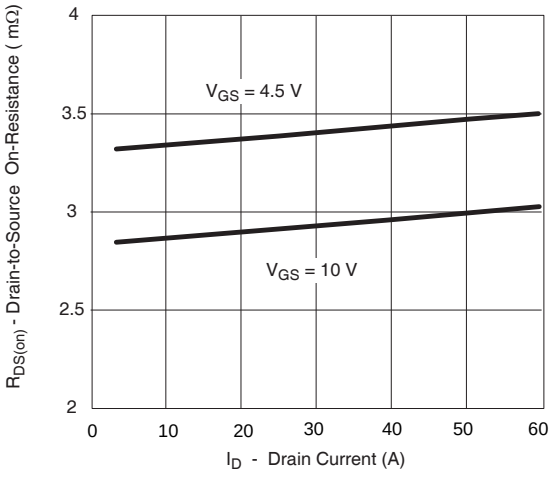
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



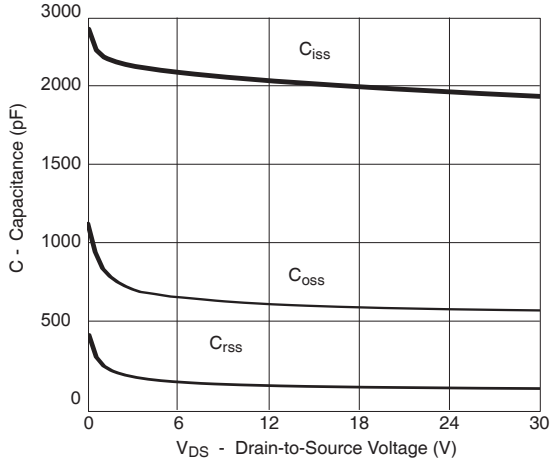
Output Characteristics



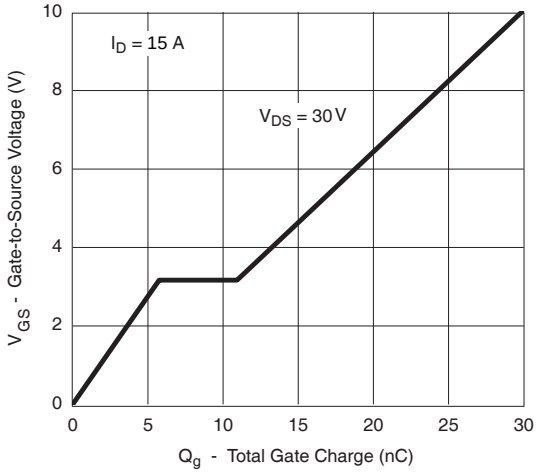
Transfer Characteristics



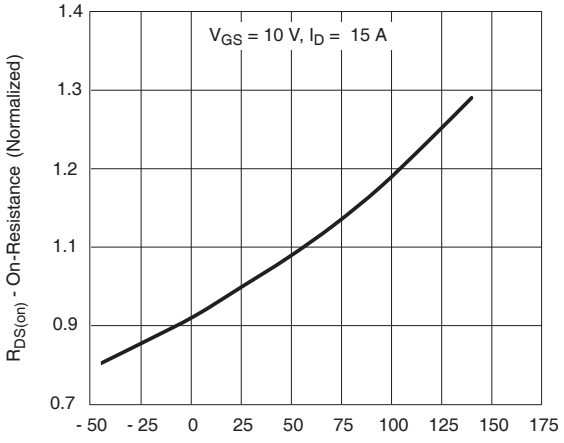
$R_{DS(on)}$ vs. Drain Current



Capacitance

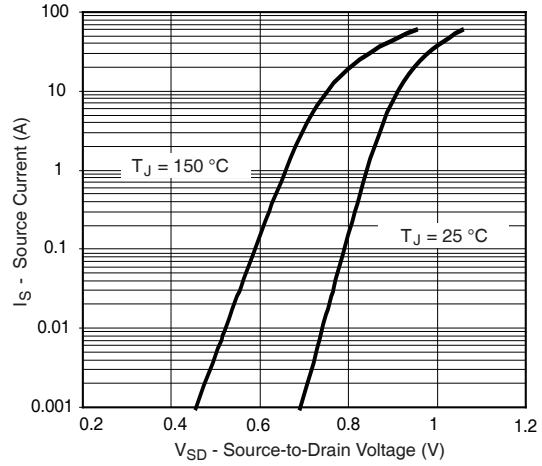


Gate Charge

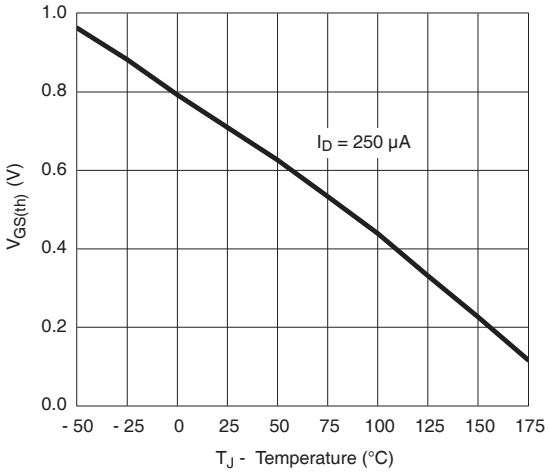


On-Resistance vs. Junction Temperature

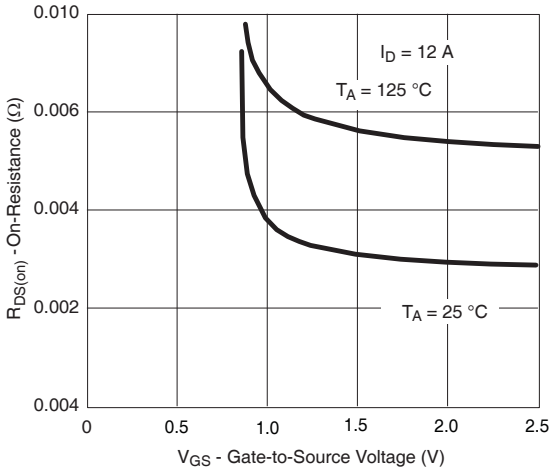
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



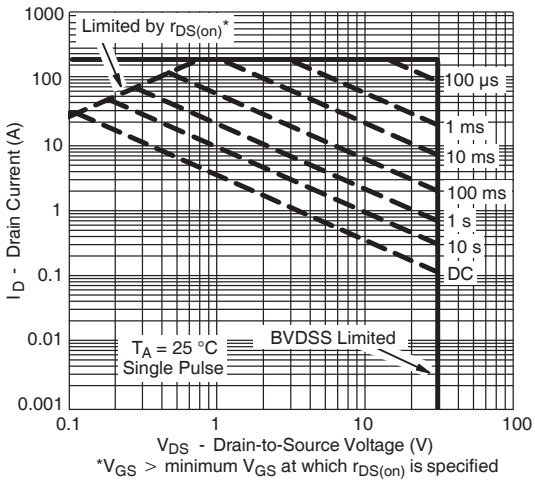
Forward Diode Voltage vs. Temperature



Threshold Voltage

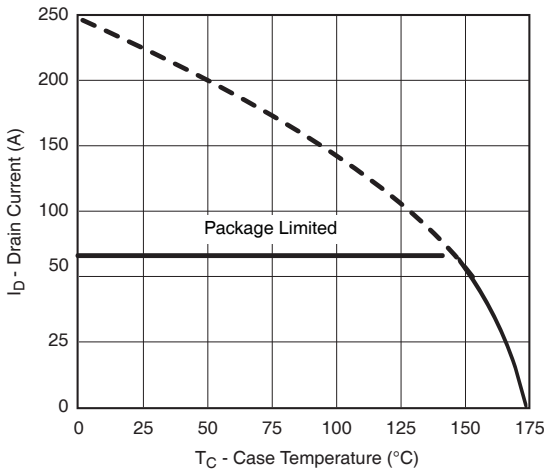


$R_{DS(on)}$ vs. V_{GS} vs. Temperature

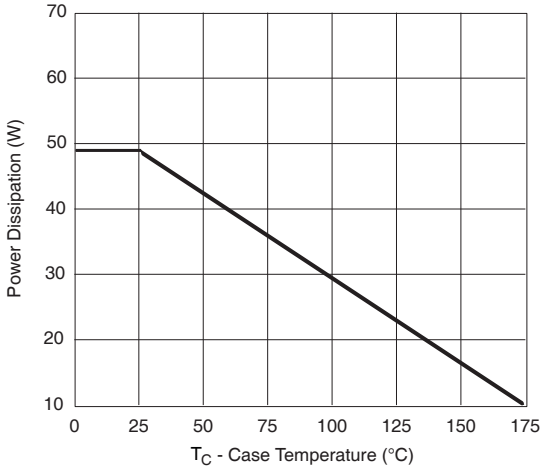


Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

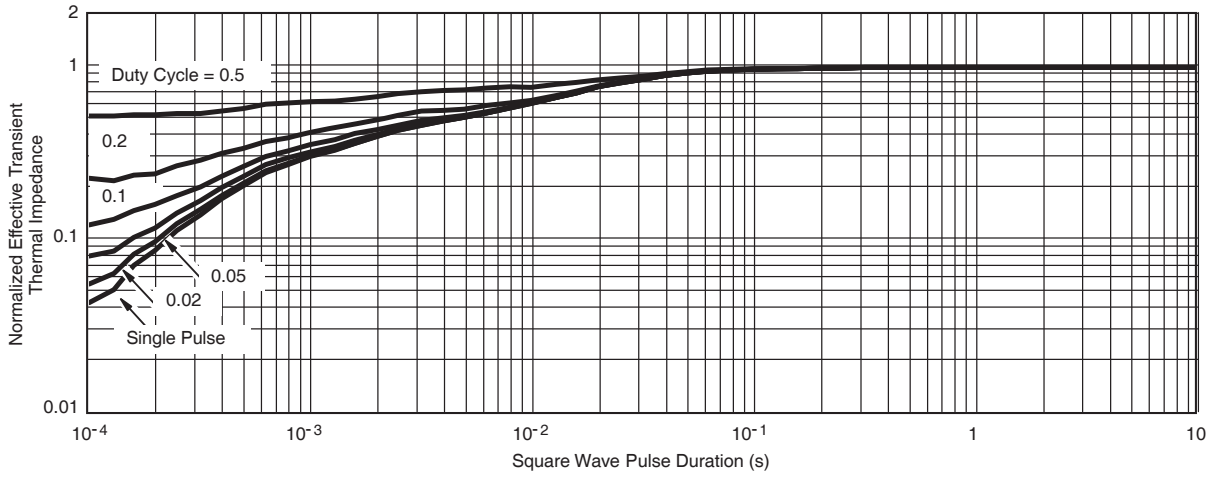


Current Derating*

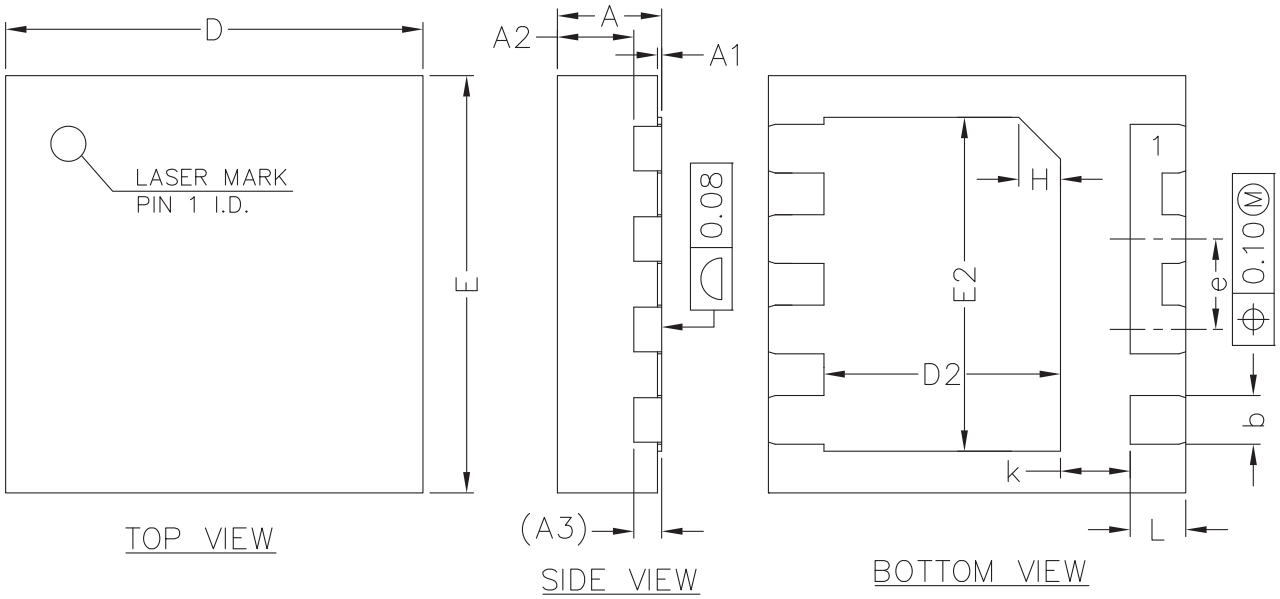


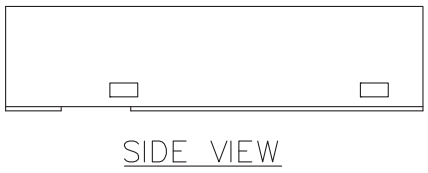
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case





COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.50	0.55	0.60
A3		0.20REF	
b	0.30	0.35	0.40
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.60	1.70	1.80
E2	2.30	2.40	2.50
e	0.55	0.65	0.75
K	0.40	0.50	0.60
L	0.35	0.40	0.45

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